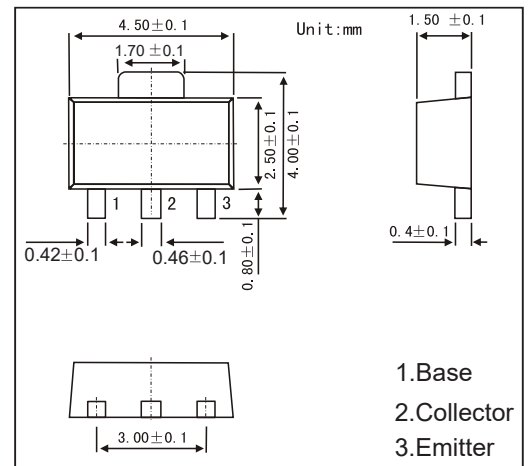


SOT-89 Plastic-Encapsulate Transistors
FEATURES

- Low collector to emitter saturation voltage
- Large current capacity and wide ASO
- Fast switching speed
- Transistors NPN

MECHANICAL DATA

- ase style:SOT-89 molded plastic
- Mounting position:any

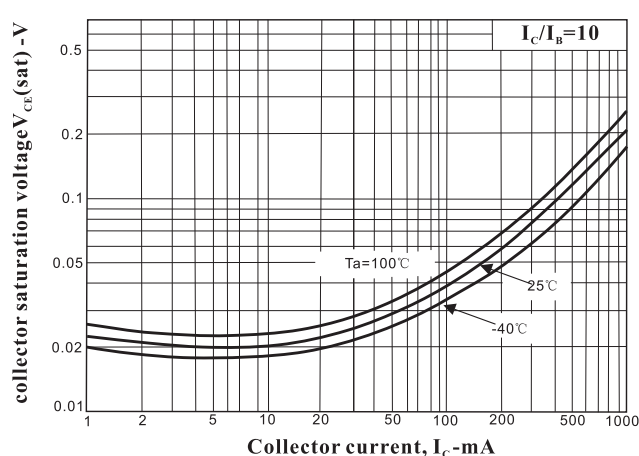
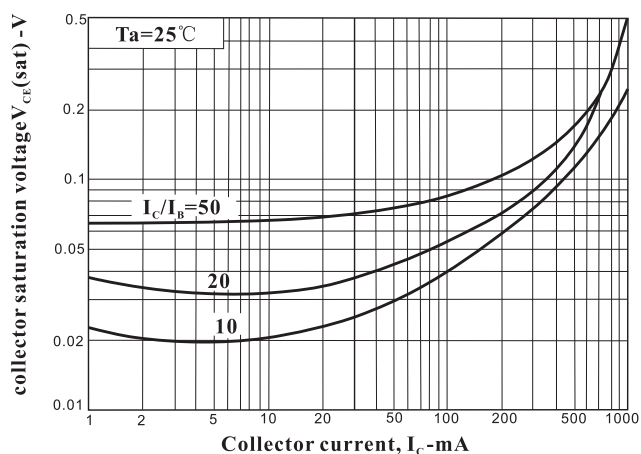
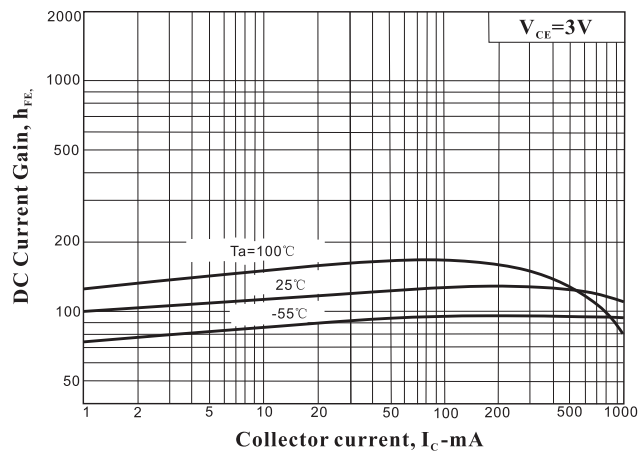
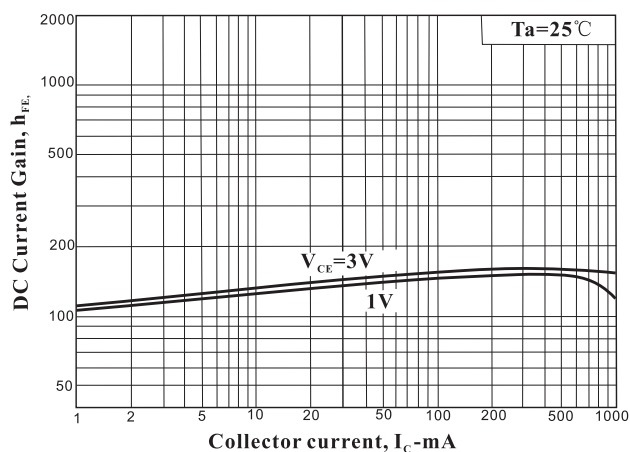
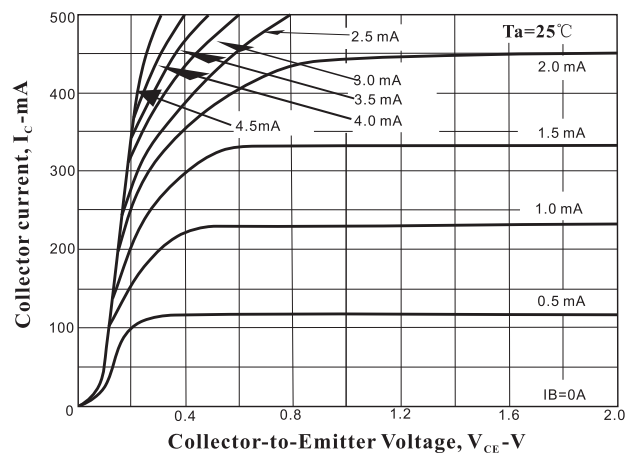
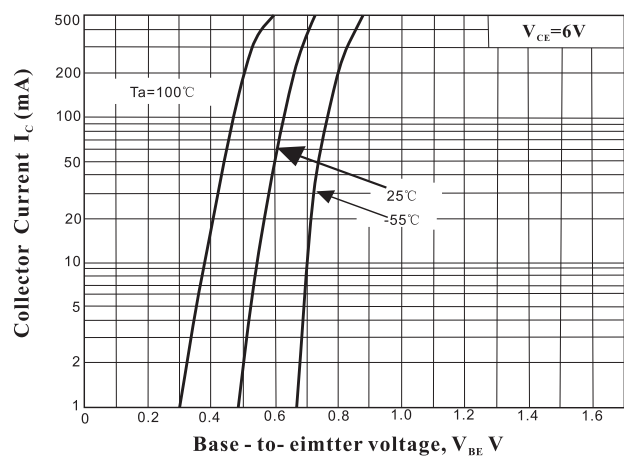

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	32	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current (DC) PW=20ms, duty=1/2	I_C	1	A
		2	A
Collector Power Dissipation	P_C	0.5	W
Junction temperature	T_j	150	°C
Storage temperature Range	T_{stg}	-55 to +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 50 \mu A, I_E = 0$	40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 mA, I_B = 0$	32			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 50 \mu A$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 20 V, I_E = 0$			0.5	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4V, I_C = 0$			0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 mA, I_B = 50 mA$		0.15	0.4	V
DC current gain	h_{FE}	$V_{CE} = 3V, I_C = 100 mA$	82		390	
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1 MHz$		15		pF
Transition frequency	f_T	$V_{CE} = 5V, I_C = 50 mA, f = 100 MHz$		150		MHz

RATINGS AND CHARACTERISTIC CURVES



RATINGS AND CHARACTERISTIC CURVES

